

**1. Material** Substrate GaAs (N Type)  
Epitaxial Layer GaAs (P/N Type)

**2. Electrode** N(Cathode) Side Gold Alloy  
P(Anode) Side Gold Alloy

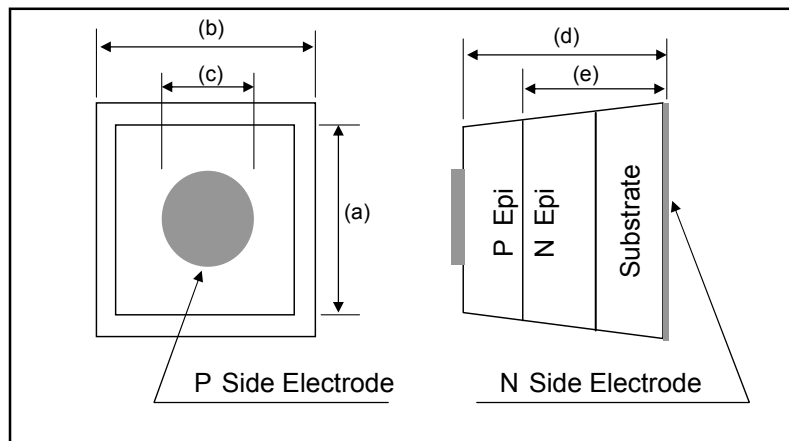
**3. Electro-Optical Characteristics**

| Parameter       | Symbol          | Min | Typ  | Max | Unit | Condition |
|-----------------|-----------------|-----|------|-----|------|-----------|
| Forward Voltage | $V_F$           |     | 1.45 | 1.7 | V    | IF=100mA  |
| Reverse Voltage | $V_R$           | 8   |      |     | V    | IR=10uA   |
| Power           | $P_O$           | 12  |      |     | mW   | IF=100mA  |
| Wavelength      | $\lambda_P$     |     | 940  |     | nm   | IF=20mA   |
|                 | $\Delta\lambda$ |     | 45   |     | nm   | IF=20mA   |

※ Note : Power is measured by Sorter E/T system with bare chip.

**4. Mechanical Data**

|                     |       |               |
|---------------------|-------|---------------|
| (a) Emission Area   | ----- | 9mil x 9mil   |
| (b) Bottom Area     | ----- | 10mil x 10mil |
| (c) Bonding Pad     | ----- | 130um         |
| (d) Chip Thickness  | ----- | 10.0mil       |
| (e) Junction Height | ----- | 6.5mil        |



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